

# FGW75N60HD

Discrete IGBT

## Discrete IGBT (High-Speed V series)

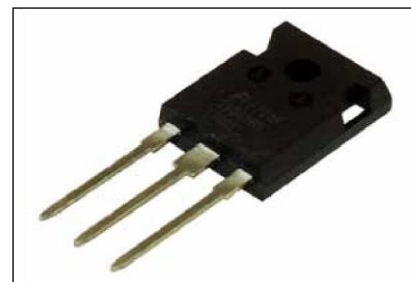
600V / 75A

### ■ Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

### ■ Applications

- Uninterruptible power supply
- Power conditioner



### ■ Equivalent circuit

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 250\mu A, V_{GE} = 0V$	600	-	-	V
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0V$	-	-	200	$\mu A$
					10	mA
Gate-Emitter Leakage Current	$I_{GES}$	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	200	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = +20V, I_C = 75mA$	4.0	5.0	6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = +15V, I_C = 75A$	-	1.00	1.90	V
			-	1.80	-	
Input Capacitance	$C_{ies}$	$V_{CE}=25V$	-	6100	-	pF
Output Capacitance	$C_{oes}$	$V_{GE}=0V$	-	300	-	
Reverse Transfer Capacitance	$C_{res}$	$f=1MHz$	-	240	-	
Gate Charge	$Q_G$	$V_{CC} = 400V$ $I_C = 75A$ $V_{GE} = 15V$	-	460	-	nC
Turn-On Delay Time	$t_{d(on)}$	$T_J = 25^\circ C$ $V_{CC} = 400V$ $I_C = 75A$ $V_{GE} = 15V$ $R_G = 10\Omega$	-	40	-	ns
Rise Time	$t_r$		-	130	-	
Turn-Off Delay Time	$t_{d(off)}$		-	400	-	
Fall Time	$t_f$		-	100	-	
Turn-On Energy	$E_{on}$		-	200	-	mJ

● Turn-Off Energy	$E_{off}$	<b>L = 500μH</b> <b>Energy loss include “tail” and FWD reverse recovery.</b>	-	ε, 2	-	
Turn-On Delay Time	$t_{d(on)}$	<b>T<sub>J</sub> = 175°C</b>	-	ε 0	-	<b>ns</b>
Rise Time	$t_r$	<b>V<sub>CC</sub> = 400V</b>	-	13.0	-	
Turn-Off Delay Time	$t_{d(off)}$	<b>I<sub>C</sub> = 75A</b>	-	ε 9.0	-	
Fall Time	$t_f$	<b>V<sub>GE</sub> = 15V</b>	-	12.0	-	
Turn-On Energy	$E_{on}$	<b>R<sub>G</sub> = 10Ω</b>	-	ε, 3	-	<b>mJ</b>
Turn-Off Energy	$E_{off}$	<b>L = 500μH</b> <b>Energy loss include “tail” and FWD reverse recovery.</b>	-	ε, 8	-	

● Power factor correction circuit

## Maximum Ratings and Characteristics

Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

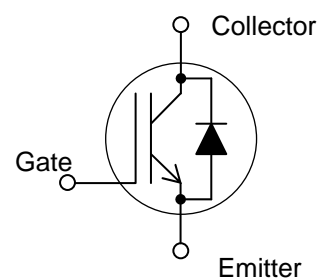
Items	Symbols	Characteristics	Units	Remarks
Collector-Emitter voltage	V <sub>CES</sub>	600	V	
Gate-Emitter voltage	V <sub>GES</sub>	±20	V	
DC Collector Current	I <sub>C@25</sub>	100	A	T <sub>C</sub> =25°C, T <sub>J</sub> =150°C Note *1
	I <sub>C@100</sub>	70	A	T <sub>C</sub> =100°C, T <sub>J</sub> =150°C
Pulsed Collector Current	I <sub>CP</sub>	220	A	Note *2
Turn-Off Safe Operating Area	-	220	A	V <sub>CE</sub> ≤600V, T <sub>J</sub> ≤175°C
Diode Forward Current	I <sub>F@25</sub>	60	A	Note *1
	I <sub>F@100</sub>	30	A	
Diode Pulsed Current	I <sub>FP</sub>	220	A	Note *1
Short Circuit Withstand Time	t <sub>sc</sub>	0	μs	V <sub>CC</sub> ≤300V, V <sub>GE</sub> =12V T <sub>J</sub> ≤175°C
IGBT Max. Power Dissipation	P <sub>D_IGBT</sub>	0.0	W	T <sub>C</sub> =25°C
FWD Max. Power Dissipation	P <sub>D_FWD</sub>	19.0		T <sub>C</sub> =25°C
Operating Junction Temperature	T <sub>J</sub>	-50~+170	°C	
Storage Temperature	T <sub>stg</sub>	-50~+170	°C	

Note \*1 : Current value limited by bonding wire. Note \*2 : Pulse width limited by T<sub>Jmax</sub>.

● Electrical characteristics (at T<sub>J</sub>= 25°C unless otherwise specified)

### FWD Characteristics

Description	Symbol	Conditions	Characteristics			Unit
			min.	typ.	max.	
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =35A T <sub>J</sub> =25°C	-	2.0	2.6	V
			-	1.4	-	V
Diode Reverse Recovery Time	t <sub>rr1</sub>	V <sub>CC</sub> =30V, I <sub>F</sub> = 3.5A - di/dt=200A/μs	-	26	36	ns



Diode Reverse Recovery Time	$t_{rr2}$	$V_{CC}=400V$ $I_F=35A$		0.00	-	$\mu s$
Diode Reverse Recovery Charge	$Q_{rr}$	$-di_F/dt=200A/\mu s$ $T_J=25^\circ C$	-	0.12	-	$\mu C$
Diode Reverse Recovery Time	$t_{rr2}$	$V_{CC}=400V$ $I_F=35A$	-	0.19	-	$\mu s$
Diode Reverse Recovery Charge	$Q_{rr}$	$-di_F/dt=200A/\mu s$ $T_J=175^\circ C$	-	1.10	-	$\mu C$

## Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	-	0.0	$^\circ C/W$
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	-	0.298	
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	-	0.781	

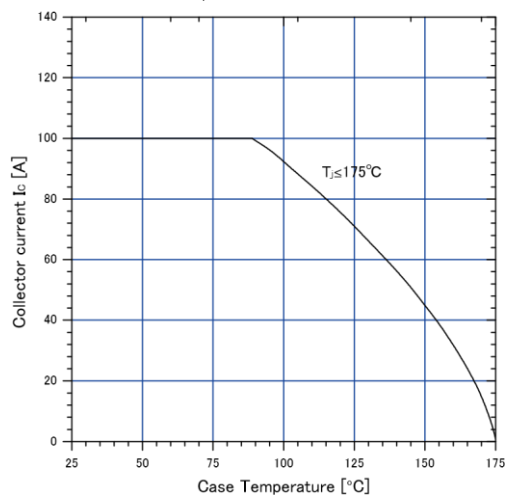


## ■ Characteristics (Representative)

**Graph.1**

**DC Collector Current vs  $T_c$**

**$V_{GE} \geq +15V$ ,  $T_i \leq 175^\circ C$**

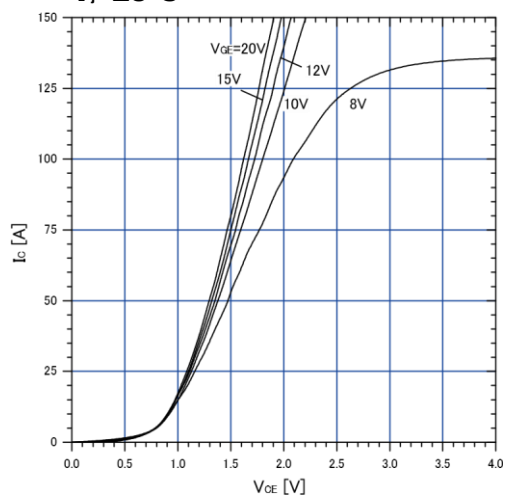


**Graph.3**

**Typical Output**

**Characteristics ( $V_{CE}-I_c$ )**

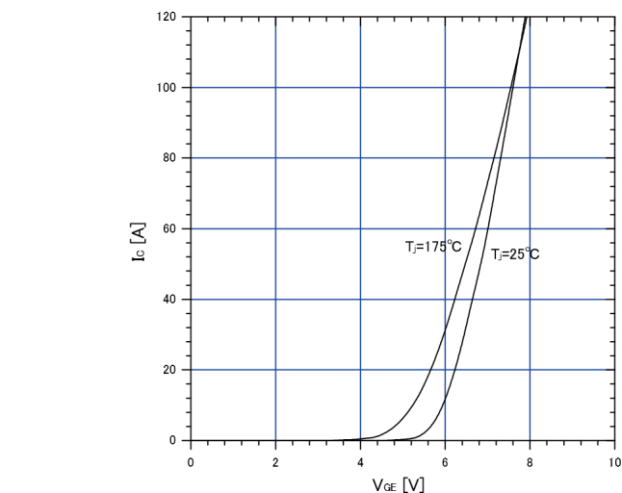
**$T_i = 25^\circ C$**



**Graph.5**

**Typical Transfer**  
**Characteristics**

**$V_{GE} = +15V$**

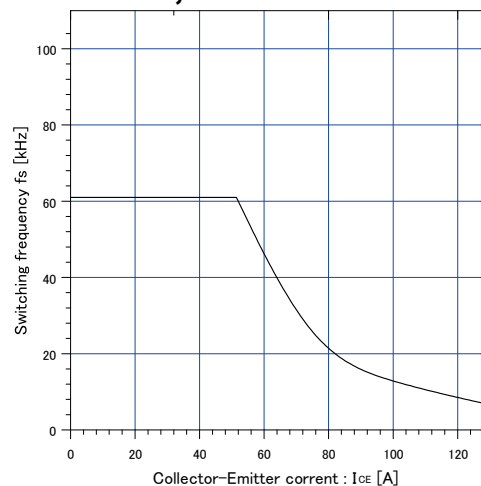


**Graph.2**

**Collector Current vs. switching**  
**frequency**

**$V_{GE} = +15V$ ,  $T_c \leq 175^\circ C$ ,  $V_{CC} = 400V$ ,  
 **$D = 0.5$ ,****

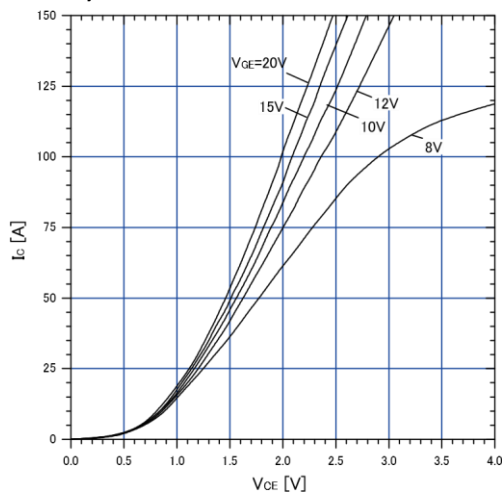
**$R_o = 10\Omega$ ,  $T_c = 100^\circ C$**



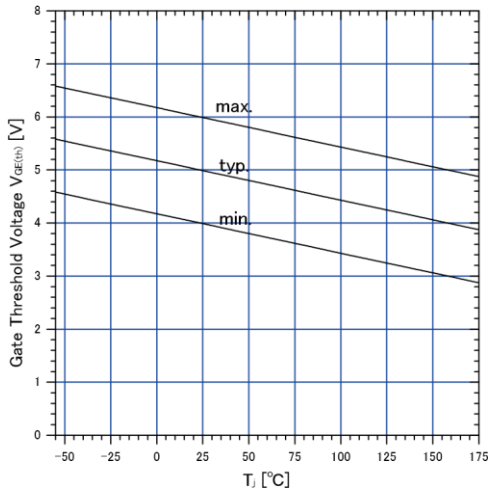
**Graph.4**

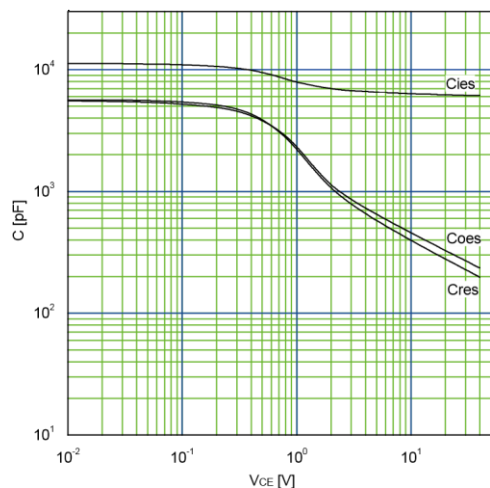
**Typical Output Characteristics**  
**( $V_{CE}-I_c$ )**

**$T_i = 175^\circ C$**



**Graph.6**  
**Gate Threshold Voltage vs. T<sub>J</sub>**  
**I<sub>C</sub>=75mA, V<sub>CE</sub>=20V**



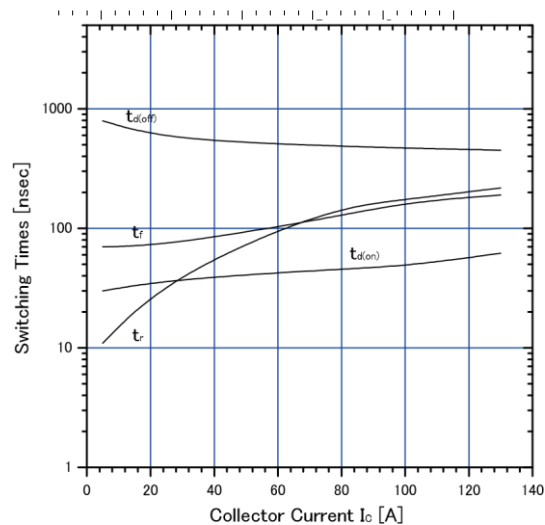


**Graph.7**  
**Typical Capacitance**

$V_{GE}=0V$ ,  $f=1MHz$ ,  $T_J=25^{\circ}C$

**Graph.9**  
**Typical switching time vs.  $I_c$**

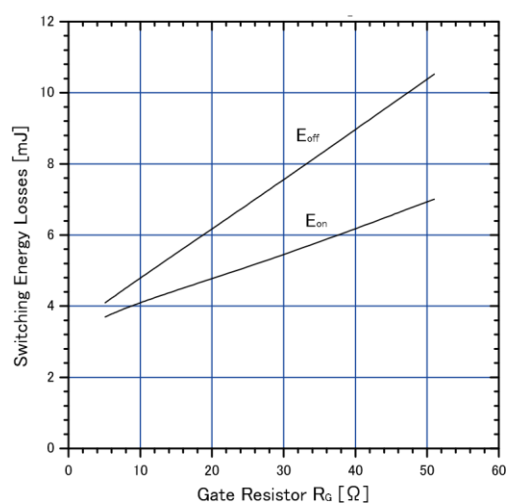
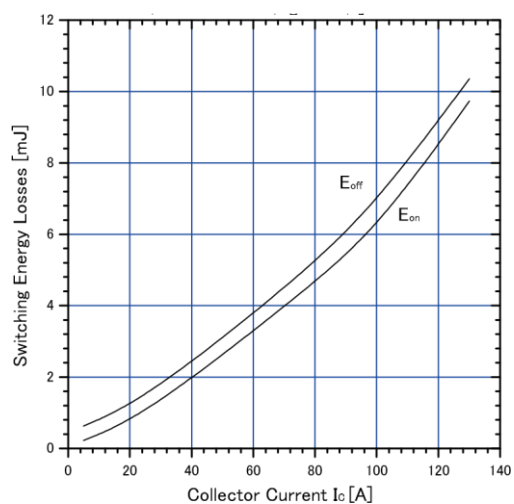
$T_J=175^{\circ}C$ ,  $V_{CC}=400V$ ,  
 $L=500\mu H$   
 $V_{GE}=15V$ ,  $R_G=10\Omega$

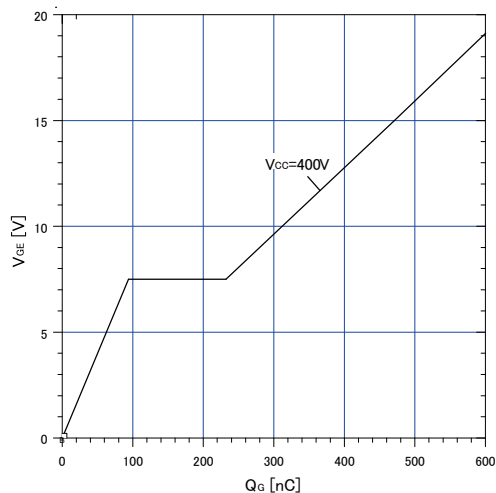


**Graph.8**  
**Typical Gate Charge**

$V_{CC}=400V$ ,  $I_c=75A$ ,  $T_J=25^{\circ}C$  losses vs.  $I_c$

$T_J=175^{\circ}C$ ,  $V_{CC}=400V$ ,  $L=500\mu H$   
 $V_{GE}=15V$ ,  $R_G=10\Omega$

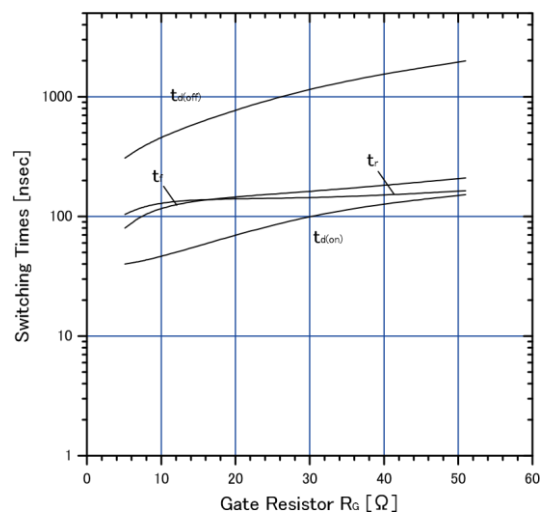




**Graph.10**

**Typical switching time vs.  
 $R_g$**

**$T_j=175^{\circ}\text{C}$ ,  $V_{cc}=400\text{V}$ ,  
 $I_c=75\text{A}$ ,  $L=500\mu\text{H}$   
 $V_{ge}=15\text{V}$**



**Graph.12**

**Typical switching losses vs.  $R_g$**

**$T_j=175^{\circ}\text{C}$ ,  $V_{cc}=400\text{V}$ ,  $I_c=75\text{A}$ ,  
 $L=500\mu\text{H}$**

**$V_{ge}=15\text{V}$**

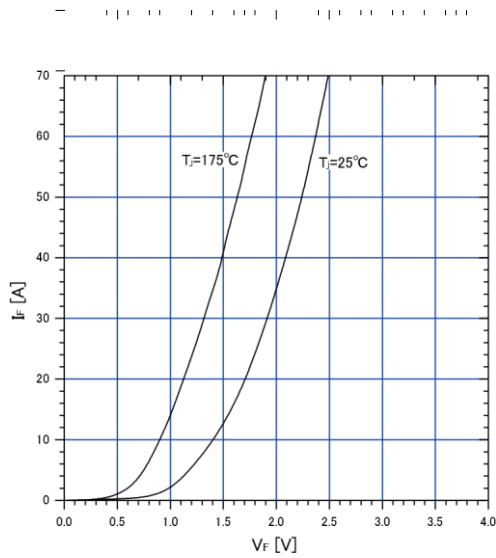
**Graph.13**

**FWD Forward voltage drop ( $V_f-I_f$ )**

**Graph.14**

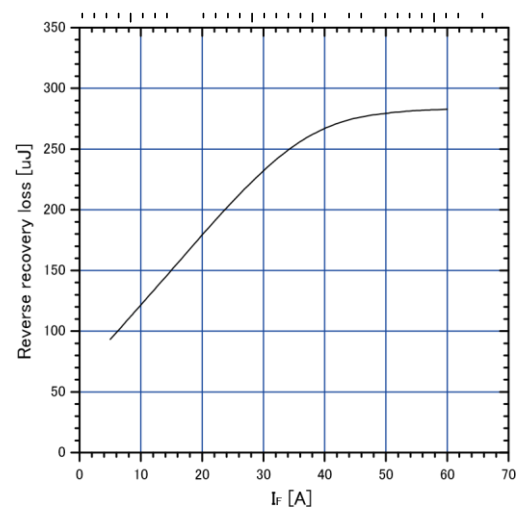
**Typical reverse recovery  
characteristics vs.  $I_r$**





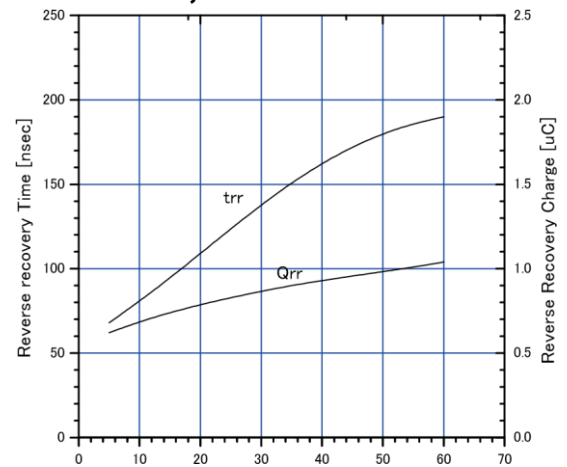
**Graph.15**  
**Typical reverse recovery**  
**loss vs.  $I_F$**

**$T_J = 175^\circ\text{C}$ ,  $V_{CC} = 400\text{V}$ ,  
 $L = 500\mu\text{H}$   
 $V_{GE} = 15\text{V}$ ,  $R_G = 10\Omega$**



**$T_J = 175^\circ\text{C}$ ,  $V_{CC} = 400\text{V}$ ,  $L = 500\mu\text{H}$**

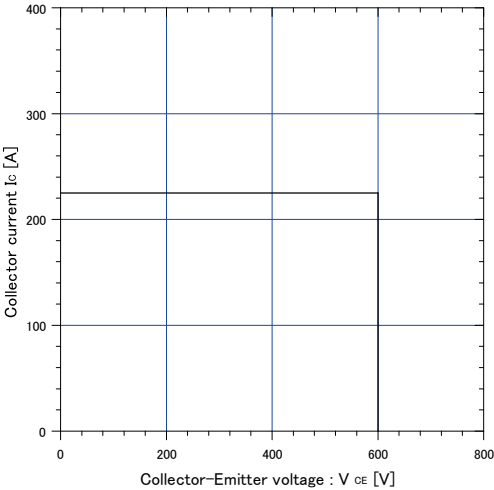
**$V_{GE} = 15\text{V}$ ,  $R_G = 10\Omega$**



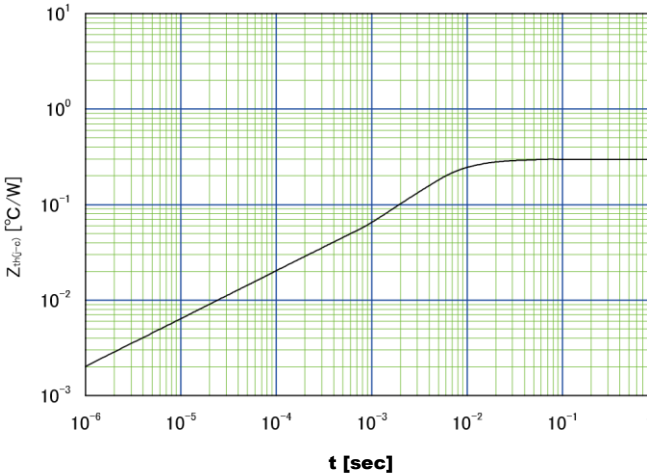
$I_F$  [A]

**Graph.16**  
**Reverse biased Safe**  
**Operating Area**

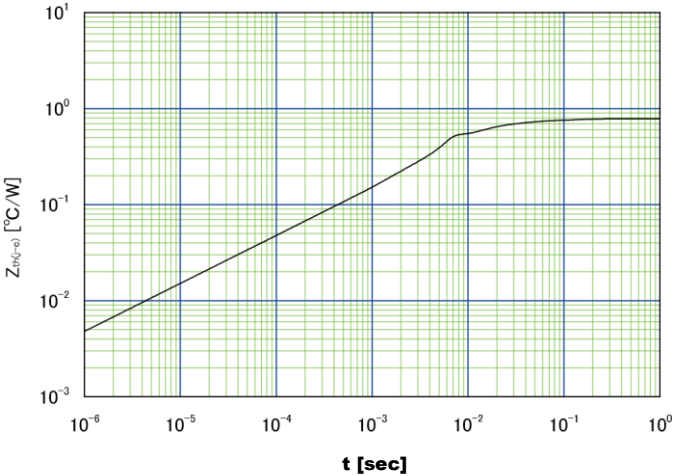
$T_J \leq 175^{\circ}\text{C}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  
 $R_G = 10\Omega$



**Graph.17 Transient thermal**  
**resistance of IGBT**

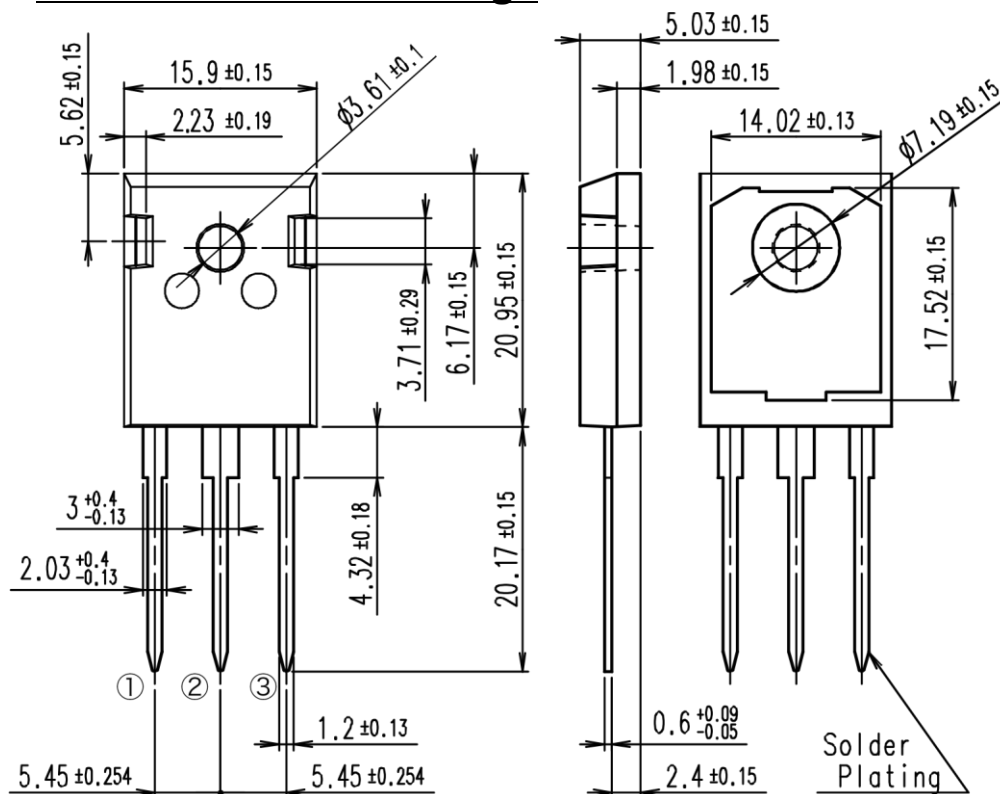


**Graph.18 Transient thermal**  
**resistance of FWD**



## ■ Outline Drawings, mm

### Outview : TO-247 Package

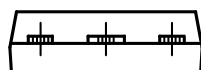


#### CONNECTION

① GATE

② COLLECTOR

③ EMITTER



① ② ③

DIMENSIONS ARE IN MILLIMETERS.

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